

EKOWEISS Semiconductors

EKOWEISS Semiconductors

Thyristor High Voltage, Phase Control SCR, 70 A



PRIMARY CHARACTERISTICS				
I _{T(AV)}	70 A			
V _{DRM} /V _{RRM}	1200 V, 1600 V			
V_{TM}	1.25 V			
I _{GT}	100 mA			
T_J	-40 °C to +125 °C			
Package	Super TO-247			
Circuit configuration	Single SCR			

FEATURES

- · High surge capability
- High voltage input rectification
- Designed and qualified according to JEDEC®-JESD 47
- Material categorization: for definitions of compliance please see EKOWEISS Semiconductors







APPLICATIONS

- · AC switches
- High voltage input rectification (soft start)
- High current crow-bar
- Other phase-control circuits
- Designed to be used with EKOWEISS input diodes, switches, and output rectifiers which are available in identical package outlines

DESCRIPTION

The EKS-70TPS.. PbF high voltage series of silicon controlled rectifiers are specifically designed for high and medium power switching, and phase control applications.

MAJOR RATINGS AND CHARACTERISTICS					
PARAMETER	TEST CONDITIONS	VALUES	UNITS		
I _{T(AV)}	Sinusoidal waveform	70	^		
I _{RMS}	Lead current limitation	75	Α		
V _{RRM} /V _{DRM}	Range	1200 to 1600	V		
I _{TSM}		1100	А		
V _T	100 A, T _J = 25 °C	1.4	V		
dV/dt		500	V/µs		
dl/dt		150	A/μs		
TJ		-40 to +125	°C		

VOLTAGE RATINGS						
PART NUMBER	V _{RRM} /V _{DRM} , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	I _{RRM} /I _{DRM} AT 125 °C mA			
EKS-70TPS12APbF	1200	1300	15			
EKS-70TPS16APbF	1600	1700	13			

Revision: 05-Jun-2020 1 Document Number: 94391

EKOWEISS

EKS-70TPS12APbF, EKS-70TPS16APbF High Voltage Series

EKOWEISS Semiconductors

EKOWEISS Semiconductors

PARAMETER PARAMETER	SYMBOL	-	EST CONDITIONS		VALUES	UNITS
			TEST CONDITIONS			UNITS
Maximum average on-state current	I _{T(AV)}	$I_C = 82 ^{\circ}C$, $180 ^{\circ}$ con	duction half sine wave		70	
Maximum continuous RMS on-state current as AC switch	I _{T(RMS)}	Lead current limitation	Lead current limitation		75	Α
Maximum peak, one-cycle	I	10 ms sine pulse, rat	ed V _{RRM} applied		930	
non-repetitive surge current	I _{TSM}	10 ms sine pulse, no	voltage reapplied		1100	†
Maximum I ² t for fusing	l ² t	10 ms sine pulse, rat	ed V _{RRM} applied	Initial T _J = T _J maximum	4325	A ² s
Maximum I-t for fusing	1-1	10 ms sine pulse, no	10 ms sine pulse, no voltage reapplied			A-S
Maximum I ² √t for fusing	I ² √t	t = 0.1 ms to 10 ms, no voltage reapplied			61 150	A²√s
Low level value of threshold voltage	V _{T(TO)1}				0.916	V
High level value of threshold voltage	V _{T(TO)2}	T 105 °C			1.21	
Low level value of on-state slope resistance	r _{t1}	T _J = 125 °C		4.138	mΩ	
High level value of on-state slope resistance	r _{t2}				3.43	1115.2
Maximum peak on-state voltage	V_{TM}	100 A, T _J = 25 °C			1.4	V
Maximum rate of rise of turned-on current	dI/dt	T _J = 25 °C		150	A/µs	
Maximum holding current	I _H	Anode supply = 6 V, resistive load, initial I_T = 1 A, T_J = 25 °C			200	
Maximum latching current	ΙL	Anode supply = 6 V, resistive load, T _J = 25 °C		400	^	
Manipular and disast last as a superior	I _{RRM} /I _{DRM}	T _J = 25 °C	$V_{R} = \text{rated V}_{RRM}/V_{DRM}$ $(T_{J} = T_{J} \text{ max., linear to } 80 \%$ $V_{DRM} = R_{g} - k = \text{open})$		1.0	mA
Maximum reverse and direct leakage current		T _J = 125 °C			15	1
Maximum rate of rise of off-state voltage	dV/dt	T _J = 125 °C			500	V/µs

TRIGGERING					
PARAMETER	SYMBOL		TEST CONDITIONS	VALUES	UNITS
Maximum peak gate power	P_{GM}	T = 30 µs		10	W
Maximum average gate power	P _{G(AV)}	1 = 30 μs		2.5	VV
Maximum peak gate current	I _{GM}			2.5	Α
Maximum peak negative gate voltage	-V _{GM}			10	
		T _J = - 40 °C		1.8	V
Maximum required DC gate voltage to trigger	V_{GT}	T _J = 25 °C	Anode supply = 6 V resistive load	1.5	·
		T _J = 125 °C		1.1	
		T _J = - 40 °C		150	
Maximum required DC gate current to trigger	I _{GT}	T _J = 25 °C	Anode supply = 6 V resistive load	100	mA
		T _J = 125 °C		80	
Maximum DC gate voltage not to trigger	V_{GD}	T = 195 °C V = roted value		0.25	V
Maximum DC gate current not to trigger	I _{GD}	T _J = 125 °C, V _{DRM} = rated value		6	mA

Revision: 05-Jun-2020 2 Document Number: 94391

EKOWEISS Semiconductors

EKOWEISS Semiconductors

THERMAL AND MECHANICAL SPECIFICATIONS						
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum junction temperature	range	TJ		-40 to +125	°C	
Maximum storage temperature	range	T _{Stg}		-40 to +150		
Maximum thermal resistance, junction to case		R _{thJC}	DC operation	0.27		
Maximum thermal resistance, junction to ambient		R _{thJA}		40	°C/W	
Typical thermal resistance, case to heatsink		R _{thCS}	Mounting surface, smooth and greased	0.2		
A				6	g	
Approximate weight				0.21	OZ.	
Mounting torque	minimum			6 (5)	kgf · cm	
Mounting torque	maximum			12 (10)	(lbf · in)	
Marking device			Casa style Super TO 247	70TPS	12APBF	
			Case style Super TO-247	70TPS	70TPS16APBF	

ΔR_{thJ-hs} conduction per junction											
DEVICE	S	SINE HALF WAVE CONDUCTION RECTANGULAR WAVE CONDUCTION						UNITS			
DEVICE	180°	120°	90°	60°	30°	180°	120°	90°	60°	30°	UNITS
VS-70TPSPbF	0.078	0.092	0.117	0.172	0.302	0.053	0.092	0.125	0.180	0.306	°C/W

Note

• The table above shows the increment of thermal resistance R_{thJ-hs} when devices operate at different conduction angles than DC

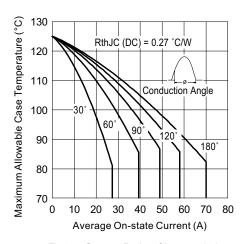


Fig. 1 - Current Rating Characteristics

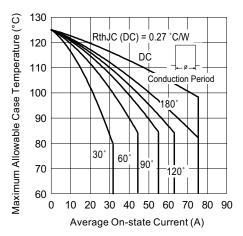


Fig. 2 - Current Rating Characteristics

EKOWEISS Semiconductors

EKOWEISS Semiconductors

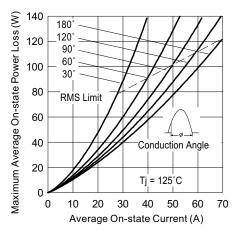


Fig. 3 - On-State Power Loss Characteristics

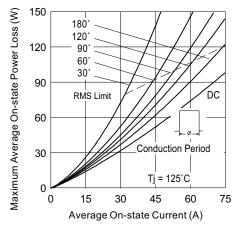


Fig. 4 - On-State Power Loss Characteristics

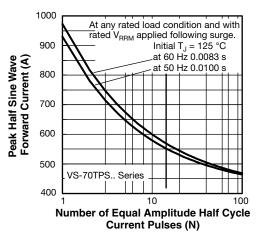


Fig. 5 - Maximum Non-Repetitive Surge Current

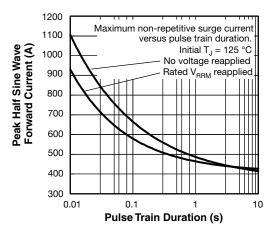


Fig. 6 - Maximum Non-Repetitive Surge Current

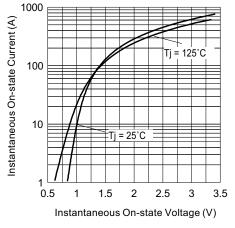


Fig. 7 - On-State Voltage Drop Characteristics

EKOWEISS Semiconductors

EKOWEISS Semiconductors

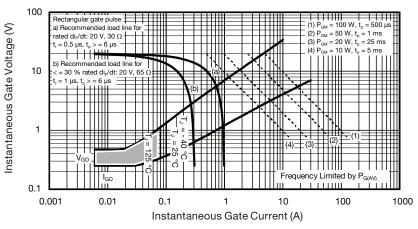


Fig. 8 - Gate Characteristics

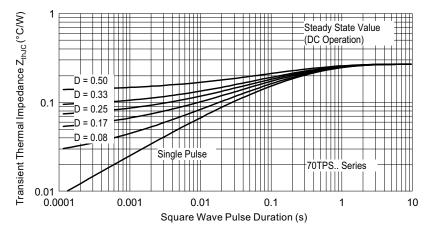


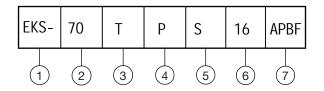
Fig. 9 - Thermal Impedance Z_{thJC} Characteristics

EKOWEISS Semiconductors

EKOWEISS Semiconductors

ORDERING INFORMATION TABLE

Device code



Vishay Semiconductors product

2 - Current rating (70 = 70 A)

3 - Circuit configuration:

T = thyristor

4 - Package:

P = super TO-247

5 - Type of silicon:

S = standard recovery rectifier

- Voltage code x 100 = V_{RRM} 12 = 1200 V 16 = 1600 V

7 - APbF = lead (Pb)-free

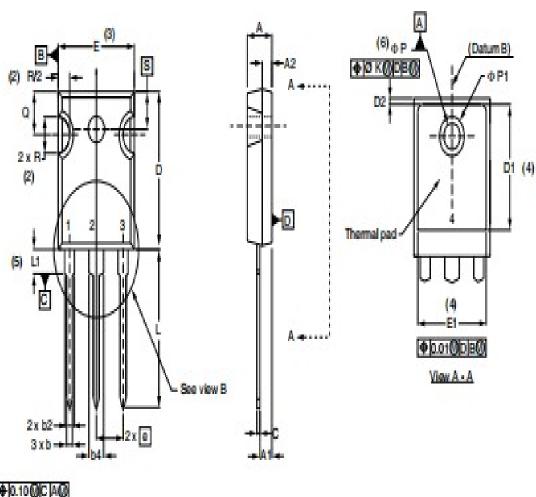
ORDERING INFORMATION (example)					
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION		
EKS-70TPS12APbF	25	500	Antistatic plastic tube		
EKS-70TPS16APbF	25	500	Antistatic plastic tube		

LINKS TO RELATED DOCUMENTS				
Dimensions	EKOWEISS Semiconductors			
Part marking information	EKOWEISS Semiconductors			
SPICE model EKS-70TPS12	EKOWEISS Semiconductors			
SPICE model EKS-70TPS16	EKOWEISS Semiconductors			

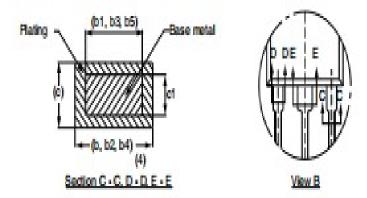
EKOWEISS Semiconductors

TO-247AD 3L

DIMENSIONS in millimeters and inches



♦0.10@C A@



Legal Disclaimer Notice

EKOWEISS

EKOWEISS Semiconductors

EKOWEISS

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Hyperlinks included in this datasheet may direct users to third-party websites. These links are provided as a convenience and for informational purposes only. Inclusion of these hyperlinks does not constitute an endorsement or an approval by Vishay of any of the products, services or opinions of the corporation, organization or individual associated with the third-party website. Vishay disclaims any and all liability and bears no responsibility for the accuracy, legality or content of the third-party website or for that of subsequent links.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.